Vishay Siliconix

Automotive Dual P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	-60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0480				
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.0612				
I _D (A) per leg	-8				
Configuration	Dual				

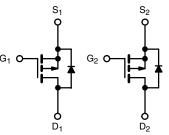
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET P-Channel MOSFET

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4917EY (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATING	iS (T _C = 25 °C, unless	otherwise noted	(k	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-60	M
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current	T _C = 25 °C	I _D	-8	
	T _C = 125 °C		-4.75	
Continuous source current (diode conduction)		I _S	-4.5	А
Pulsed drain current a		I _{DM}	-32	
Single pulse avalanche current	1 0411	I _{AS}	-22.4	
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	25	mJ
	T _C = 25 °C		5	14/
Maximum power dissipation ^a	T _C = 125 °C	P_{D}	1.67	W
Operating junction and storage temperature range		T _J , T _{sta}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	110	°C/W	
Junction-to-foot (drain)		R _{thJF}	30	C/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR-4 material)
- c. Parametric verification ongoing



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	- !	•			·		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-60	-	=	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{DS} = V _{GS} , I _D = -250 μA		-2.0	-2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1	μA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	
		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-30	-	-	Α
		V _{GS} = -10 V	$I_D = -4.3 \text{ A}$	-	0.0400	0.0480	Ω
Duain aguras en etete vacietence 3	D	V _{GS} = -10 V	I _D = -4.3 A, T _J = 125 °C	-	-	0.0780	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -4.3 A, T _J = 175 °C	-	-	0.0960	
		$V_{GS} = -4.5 \text{ V}$	$I_D = -3.8 \text{ A}$	-	0.0510	0.0612	
Forward transconductance ^b	9 _{fs}	V _{DS} =	V _{DS} = -15 V, I _D = -4.3 A		13	=	S
Dynamic ^b							
Input capacitance	C _{iss}			-	1530	1910	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = -30 V, f = 1 MHz$		334	417	рF
Reverse transfer capacitance	C _{rss}			-	114	142	•
Total gate charge ^c	Qg			-	43.4	65	
Gate-source charge ^c	Q_{gs}	$V_{GS} = -10 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -5 \text{ A}$	-	4.7	-	nC
Gate-drain charge ^c	Q _{gd}			-	9	-	
Gate resistance	R _g		f = 1 MHz		2.5	4	Ω
Turn-on delay time ^c	t _{d(on)}			-	11	17	
Rise time ^c	t _r	V_{DD} = -30 V, R_L = 8.8 Ω I_D \cong -5 A, V_{GEN} = -10 V, R_g = 1 Ω		-	11	17	- ns
Turn-off delay time ^c	t _{d(off)}			-	35	52	
Fall time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Char	racteristics b	•					
Pulsed current ^a	I _{SM}			-	_	-32	А
Forward voltage	V _{SD}	I _F = -2.8 A, V _{GS} = 0 V			-0.8	-1.2	V

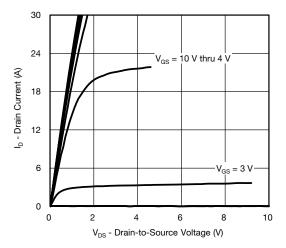
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

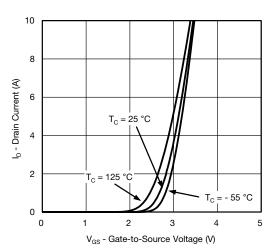
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



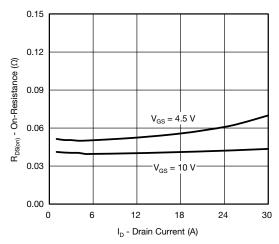
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



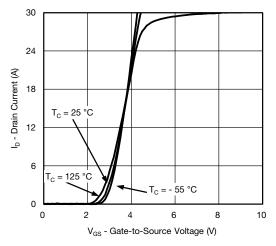
Output Characteristics



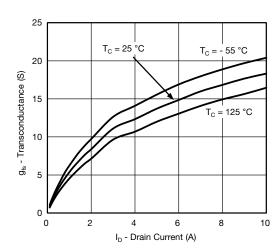
Transfer Characteristics



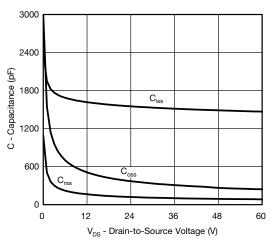
On-Resistance vs. Drain Current



Transfer Characteristics



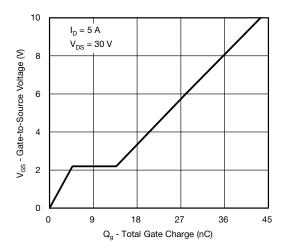
Transconductance



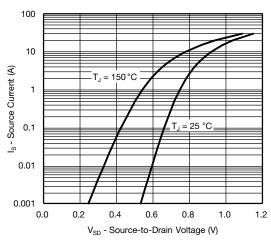
Capacitance



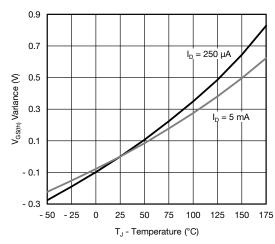
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



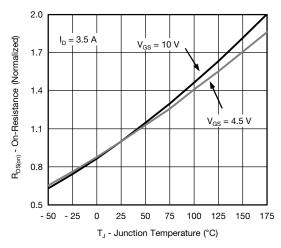
Gate Charge



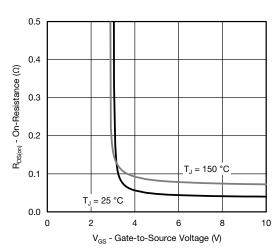
Source Drain Diode Forward Voltage



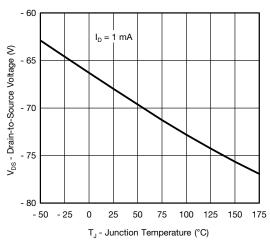
Threshold Voltage



On-Resistance vs. Junction Temperature



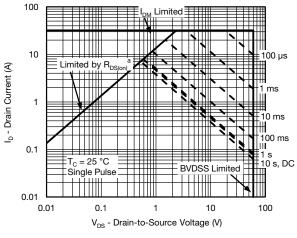
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



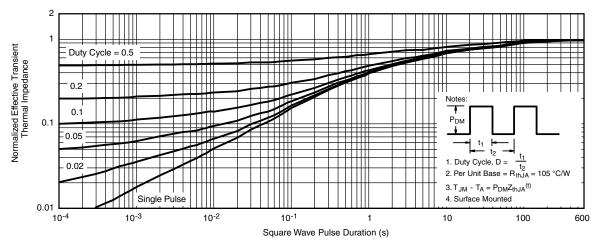
Safe Operating Area

Note

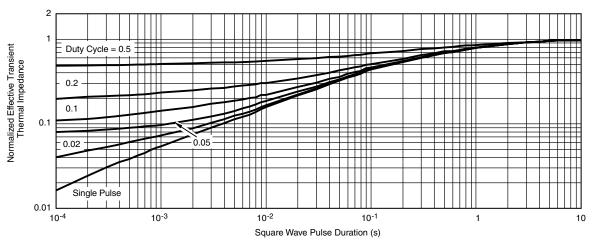
a. $V_{GS} > minimum \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62785.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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